



T16M35T600B(LS)

Triacs Silicon Bidirectional Thyristors

TRIACS 16 AMPERES RMS 600 VOLTS

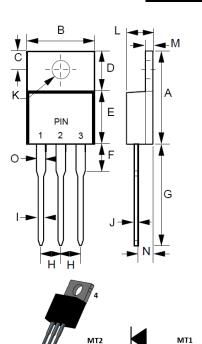
TO-220AB

FEATURES

- Blocking voltage to 600V
- Minimizes Snubber Networks for Protection
- On-State Current Rating of 16 Amperes RMS High surge Current Capability - 150 Amperes
- Glass Passivated Junctions for Reliability and Uniformity Operational in Three Quadrants, Q1, Q2, and Q3
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

MECHANICAL DATA

- Package: TO-220AB
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Terminals: Finish Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (c3)
- Weight: 0.07 ounces, 2.0 grams (Approximate)



TO-220AB DIM. MIN. MAX Α 14.22 15.88 В 9.65 10.67 С 2.54 3.43 D 5.84 6.86 Ε 8.26 9.28 F 6.35 G 12.70 14.73 н 2.29 2.79 Т 0.51 1.14 J 0.40 0.67 Κ 3.53Ø 4.09Ø 4.83 3.56 L Μ 1.40 1.14 Ν 2.03 2.92 0 1.17 1.37 All Dimensions in millimeter.

PIN ASSIGNMENT1Main terminal 12Main terminal 23Gate4Main terminal 2

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at +25°C ambient temperature unless otherwise specified.

MAXIMUM RATINGS

PARAMETER		VALUE	UNIT
Peak repetitive off-state voltage (TJ = -40 to +125°C, sine wave, 50 to 60Hz; gate open)	Vdrm Vrrm	600 600	Volts
On-stage RMS current (full sine wave 50 to 60Hz, T_c = +80°C)	I _{T(RMS)}	16	Amp
Peak non-repetitive surge current (one full cycle 60Hz, T_J = +25°C)	Itsm	150	Amps
Circuit fusing consideration (t = 8.3ms)	l ² t	93	A ² s
Operating junction temperature range	TJ	-40 to +125	°C
Storage temperature range	Тѕтс	-40 to +150	°C

Notes:

1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.



LITE-ON SEMICONDUCTOR

OFF CHARACTERISTICS

PARAMETER		SYMBOL	МАХ	UNIT
Peak repetitive forward or reverse blocking current (V_{AK} = rated V_{DRM} and V_{RRM} , gate open)	T」= +25°C T」= +125°C	Idrm Irrm	0.01 2.0	mA

ON CHARACTERISTICS

PARAMETER	SYMBOL	МАХ	UNIT
Peak forward on-state voltage ($I_{TM} = \pm 16A @ t_P \le 2.0ms$, duty cycle $\le 2\%$)	Vtm	1.6	Volts
Gate trigger current $(V_D = 12V, R_L = 100\Omega)$	I _{GT1} IGT2 I _{GT3}	35 35 35	mA
Gate trigger voltage $(V_D = 12V, R_L = 100\Omega)$	V _{GT1} V _{GT2} V _{GT3}	1.5 1.5 1.5	Volts
Holding current $(V_D = 12V, initiation current = \pm 150mA, gate open)$	Ι _Η	50	mA
Latching current $(V_D = 12V, I_G = 35mA)$	L1 L2 L3	50 80 50	mA

DYNAMIC CHARACTERISTICS

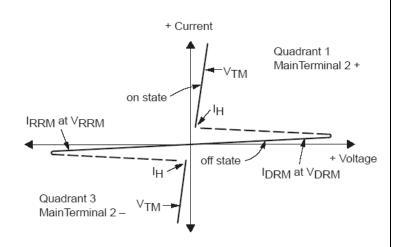
PARAMETER	SYMBOL	MIN	UNIT
Critical rate of rise of Commutation voltage $V_D = 67\%$ rated V_{DRM} , exponential waveform, $T_C = +125$ °C	dv/dt	600	V/µs



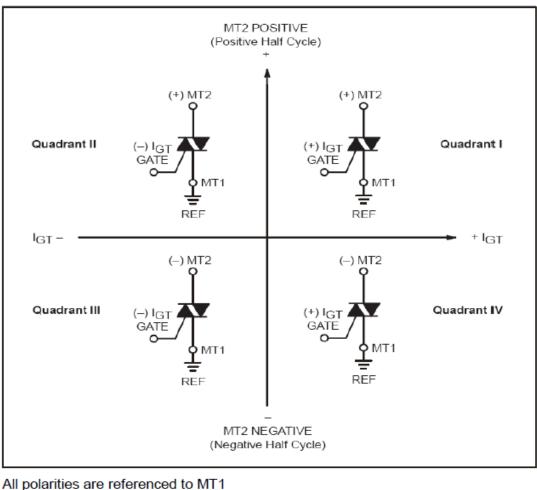
RATING AND CHARACTERISTIC CURVES T16M35T600B(LS)

LITE-ON SEMICONDUCTOR

Symbol	Parameter
VDRM	Peak Repetitive Forward Off State Voltage
IDRM	Peak Forward Blocking Current
VRRM	Peak Repetitive Reverse Off State Voltage
IRRM	Peak Reverse Blocking Current
VTM	Maximum On State Voltage
ΙΗ	Holding Current



Quadrant Definitions

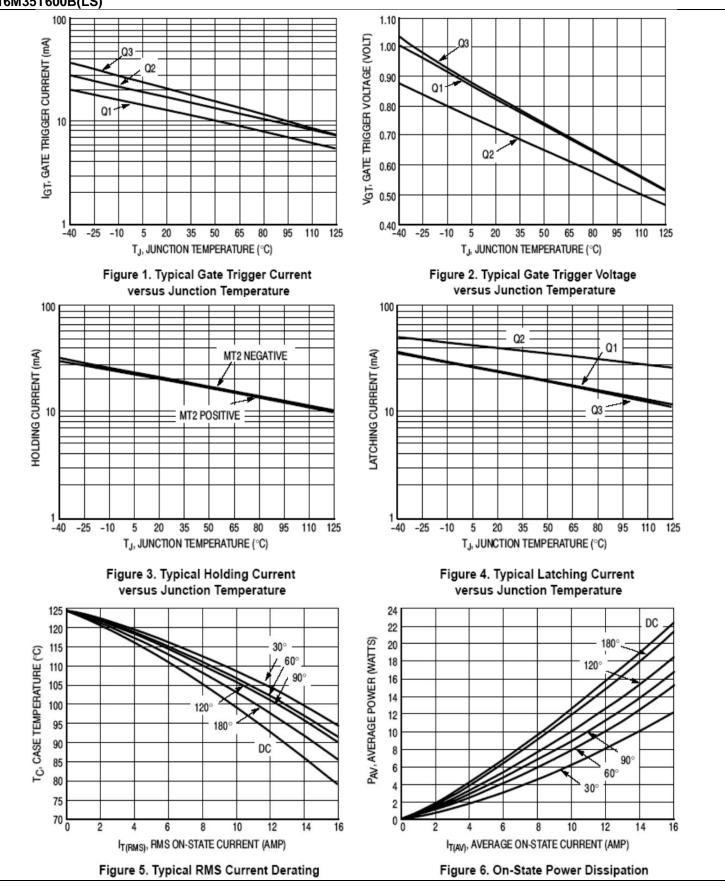


Whith in -phase signal (using standard AC lines) quadrants I and III are used



LITE-ON SEMICONDUCTOR

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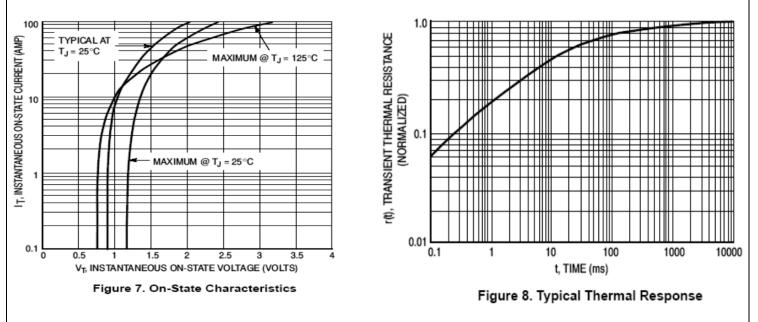




LITE-ON SEMICONDUCTOR

RATING AND CHARACTERISTIC CURVES

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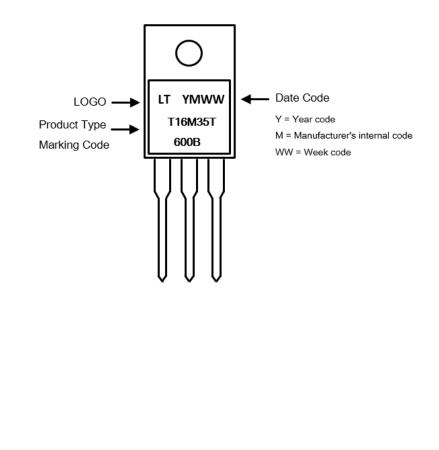




Ordering Information:

Part Number	Package	Pac	king
Fait Nulliger	Fackage	Qty.	Carrier
T16M35T600B	TO-220AB	50pcs	Tube

Marking Information:





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